







SN74LV374A

SCLS408L - MAY 1998 - REVISED MARCH 2023

SN74LV374A Octal Edge-Triggered D-Type Flip-Flops With 3-State Outputs

1 Features

- V_{CC} operation of 2 V to 5.5 V
- Maximum t_{pd} of 9.5 ns at 5 V
- Typical V_{OLP} (Output Ground Bounce) <0.8 V at $V_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2.3 V at $V_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Support Mixed-Mode Voltage Operation on All
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-up Performance Exceeds 250 mA Per JESD

2 Applications

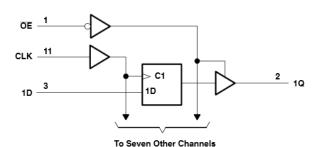
- Programmable Logic Controller (PLC)
- DCS and PAC: Analog Input Module
- Trains, Trams, and Subway Carriages
- **AC Inverter Drives**
- **Printers**

3 Description

The SN74LV374A devices are octal edge-triggered Dtype flip-flops designed for 2 V to 5.5 V V_{CC} operation.

Package Information

PART NUMBER	PACKAGE	BODY SIZE (NOM)			
	DB (SSOP, 20)	7.20 mm × 5.30 mm			
SN74LV374A	DW (SOIC, 20)	12.80 mm × 7.50 mm			
SIN/4LV3/4A	NS (SO, 20)	12.60 mm × 5.30 mm			
	PW (TSSOP, 20)	6.50 mm × 4.40 mm			



Pin numbers shown are for the DB, DW, NS, PW, and RGY packages

Logic Diagram (Positive Logic)



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Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information



5 Pin Configuration and Functions

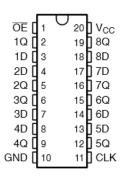


Figure 5-1. DB, DW, NS, or PW Package 20-PIN SSOP, SOIC, SO, or TSSOP (Top View)

Table 5-1. Pin Functions

	PIN	TVDE	DESCRIPTION
NAME	NO.	TYPE	DESCRIPTION
ŌĒ	1	I	Enable pin
1Q	2	0	Output 1
1D	3	I	Input 1
2D	4	I	Input 2
2Q	5	0	Output 2
3Q	6	0	Output 3
3D	7	I	Input 3
4D	8	I	Input 4
4Q	9	0	Output 4
GND	10	_	Ground pin
CLK	11	I	Clock pin
5Q	12	0	Output 5
5D	13	I	Input 5
6D	14	I	Input 6
6Q	15	0	Output 6
7Q	16	0	Output 7
7D	17	I	Input 7
8D	18	I	Input 8
8Q	19	0	Output 8
V _{CC}	20	_	Power pin



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
VI	Input voltage ⁽²⁾		-0.5	7	V
Vo	Voltage applied to any output in	Itage applied to any output in the high-impedance or power-off state (2)			
Vo	Output voltage ⁽²⁾ (3)	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	(V _I < 0)		-20	mA
I _{OK}	Output clamp current	(V _O < 0)		-50	mA
Io	Continuous output current	(V _O = 0 to V _{CC})		±35	mA
	Continuous current through V _C	_C or GND		±70	mA
T _J	Junction temperature	Junction temperature			
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V
		Machine Model (A115-A)	±200	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ This value is limited to 5.5 V maximum.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

			SN74LV37	74A	
			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	5.5	V
		V _{CC} = 2 V	1.5		
,	High lavelingust valtage	V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		V
/ _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7		V
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.77		
		V _{CC} = 2 V		0.5	
,	Laurianal importoraltana	V _{CC} = 2.3 V to 2.7 V		V _{CC} × 0.3	V
/ _{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V		V _{CC} × 0.3	
/ _I	Input voltage	,	0	5.5	V
,	Output voltage	High or low state	0	V _{CC}	V
/ ₀		3-state	0	5.5	V
		V _{CC} = 2 V		-50	μA
	LEat Issuel autout assument	V _{CC} = 2.3 V to 2.7 V		-2	
ОН	High-level output current	V _{CC} = 3 V to 3.6 V		-8	mA
		V _{CC} = 4.5 V to 5.5 V		-16	
		V _{CC} = 2 V		50	μA
		V _{CC} = 2.3 V to 2.7 V		2	
OL	Low-level output current	V _{CC} = 3 V to 3.6 V		8	mA
		V _{CC} = 4.5 V to 5.5 V		16	
		V _{CC} = 2.3 V to 2.7 V		200	
∆t/Δv	Input transition rise or fall rate	Input transition rise or fall rate V _{CC} = 3 V to 3.6 V		100	ns/V
		V _{CC} = 4.5 V to 5.5 V		20	
ΓΑ	Operating free-air temperature	1	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.4 Thermal Information

		SN74LV374A						
	THERMAL METRIC(1)	DB (SSOP)	DW (SOIC)	NS (SO)	PW (TSSOP)	UNIT		
		20 PINS	20 PINS	20 PINS	20 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	94.5	102.3	76.7	102.4	°C/W		
R _{0JC(top)}	Junction-to-case (top) thermal resistance	56.4	69.9	43.2	36.5	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	49.7	70.8	44.2	53.6	°C/W		
ΨЈТ	Junction-to-top characterization parameter	18.5	46.4	16.8	2.4	°C/W		
ΨЈВ	Junction-to-board characterization parameter	49.3	70.4	43.8	52.9	°C/W		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W		

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{cc}		LV374A to +85°C	SN74LV374A -40°C to +125°C			UNIT
			MIN	TYP MAX	MIN	TYP	MAX	
	I _{OH} = -50 μA	2 V to 5.5 V	V _{CC} -0.1		V _{CC} -0.1			
V	I _{OH} = −2 mA	2.3 V	2		2	'		V
V _{OH}	I _{OH} = -8 mA	3 V	2.48		2.48			V
	I _{OH} = -16 mA	4.5 V	3.8		3.8			
	I _{OL} = 50 μA	2 V to 5.5 V		0.1			0.1	
\	I _{OL} = 2 mA	2.3 V		0.4			0.4	V
V _{OL}	I _{OL} = 8 mA	3 V		0.44			0.44	V
	I _{OL} = 16 mA	4.5 V		0.55			0.55	
I _I	V _I = 5.5 V or GND	0 to 5.5 V		±1			±1	μA
I _{OZ}	V _O = V _{CC} or GND	5.5 V		±5			±5	μA
I _{CC}	V _I = V _{CC} or GND , I _O = 0	5.5 V		20			20	μA
I _{off}	$V_1 \text{ or } V_0 = 0 \text{ to } 5.5 \text{ V}$	0		5			5	μA
C _i	V _I = V _{CC} or GND	3.3 V		2.9		2.9		pF

6.6 Switching Characteristics, V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO	LOAD	T _A = 25°C			SN74LV374A -40°C to +85°C		SN74LV374A -40°C to +125°C		UNIT
	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
£			C _L = 15 pF	60 ⁽¹⁾	105 ⁽¹⁾		50		50		MHz
f _{max}			C _L = 50 pF	50	85		40		40		
t _{pd}	CLK	Q			9.7 ⁽¹⁾	16.3 ⁽¹⁾	1	19	1	20.5	
t _{en}	ŌĒ	Q	C _L = 15 pF		8.9 ⁽¹⁾	15.9 ⁽¹⁾	1	19	1	20.5	ns
t _{dis}	ŌĒ	Q			6.3 ⁽¹⁾	12.6 ⁽¹⁾	1	15	1	16.5	
t _{pd}	CLK	Q			11.8	19.3	1	23	1	24.5	
t _{en}	ŌĒ	Q	0 - 50 - 5		10.9	18.8	1	22	1	23.5	
t _{dis}	ŌĒ	Q	C _L = 50 pF		8.2	17.3	1	19	1	20.5	ns
t _{sk(o)}						2		2			

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

6.7 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER	FROM TO (OUTPUT)		LOAD CAPACITANCE	T _A = 25°C			SN74LV374A -40°C to +85°C		SN74LV374A -40°C to +125°C		UNIT	
	(INFOT)	(OUTFUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX		
f			C _L = 15 pF	80 ⁽¹⁾	150 ⁽¹⁾		70		70		MHz	
f _{max}			C _L = 50 pF	55	110		50		50			
t _{pd}	CLK	Q			6.8 ⁽¹⁾	12.7 ⁽¹⁾	1	15	1	16		
t _{en}	ŌĒ	Q	C _L = 15 pF		6.3 ⁽¹⁾	11 ⁽¹⁾	1	13	1	14	ns	
t _{dis}	ŌĒ	Q			4.7(1)	10.5 ⁽¹⁾	1	12.5	1	13.5		
t _{pd}	CLK	Q			8.3	16.2	1	18.5	1	19.5		
t _{en}	ŌĒ	Q	0 - 50 - 5		7.7	14.5	1	16.5	1	17.5		
t _{dis}	ŌĒ	Q	C _L = 50 pF		5.9	14	1	16	1	17	ns	
t _{sk(o)}						1.5		1.5				

⁽¹⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested.

6.8 Switching Characteristics, $V_{CC} = 5 V \pm 0.5 V$

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted)

PARAMETER	FROM TO (OUTPUT		TO LOAD (OUTPUT) CAPACITANCE		T _A = 25°C		SN74LV374A -40°C to +85°C		SN74LV374A -40°C to +125°C		UNIT	
	(1141 01)	(001701)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX		
f			C _L = 15 pF	130 ⁽¹⁾	205 ⁽¹⁾		110		110		MHz	
f _{max}			C _L = 50 pF	85	1705		75		75			
t _{pd}	CLK	Q			4.9 ⁽¹⁾	8.1 ⁽¹⁾	1	9.5	1	10.5		
t _{en}	ŌĒ	Q	$C_{L} = 15 pF$		4.6 ⁽¹⁾	7.6 ⁽¹⁾	1	9	1	10	ns	
t _{dis}	ŌĒ	Q			3.4 ⁽¹⁾	6.8 ⁽¹⁾	1	8	1	9		
t _{pd}	CLK	Q			5.9	10.1	1	11.5	1	12.5		
t _{en}	ŌĒ	Q	C = 50 = F		5.5	9.6	1	11	1	12		
t _{dis}	ŌĒ	Q	C _L = 50 pF		4	8.8	1	10	1	11	ns	
t _{sk(o)}						1		1				

⁽¹⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested.

6.9 Timing Requirements

over recommended operating free-air temperature range, (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

		T _A = 25°	°C	SN74LV374A -40°C to +85°C	SN74LV374A -40°C to +125	_	UNIT
		MIN	MAX	MIN M	AX MIN	MAX	
V _{CC} =	2.5 V ± 0.2 V						
t _w	Pulse duration, CLK high or low	6		7	7		ns
t _{su}	Setup time, data before CLK↑	5		5.5	6		ns
t _h	Hold time, data after CLK↑	2.5		2.5	3		ns
V _{CC} =	3.3 V ± 0.3 V						
t _w	Pulse duration, CLK high or low	5		5.5	5.5		ns
t _{su}	Setup time, data before CLK↑	4.5		4.5	5		ns
t _h	Hold time, data after CLK↑	2		2	2.5		ns
V _{CC} =	5 V ± 0.5 V	<u>'</u>			,	'	
t _w	Pulse duration, CLK high or low	5		5	5		ns
t _{su}	Setup time, data before CLK↑	3		3	3.5		ns
t _h	Hold time, data after CLK↑	2		2	2.5		ns



6.10 Noise Characteristics

 $V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ (1)

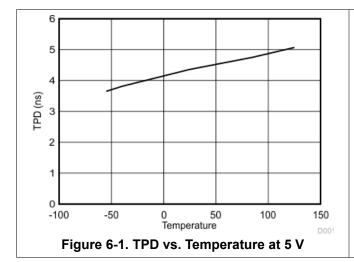
	PARAMETER	SN7	UNIT		
	PARAMETER	MIN	TYP	MAX	UNII
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.6	0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.5	-0.8	V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}	2.9	2.9		V
V _{IH(D)}	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

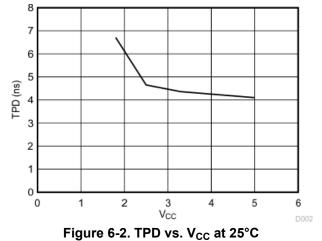
⁽¹⁾ Characteristics are for surface-mount packages only.

6.11 Operating Characteristics, T_A = 25°C

	PARAMETER		TEST CONI	DITIONS	V _{cc}	TYP	UNIT
	Power dissipation	Outputs enabled	$C_1 = 50 \text{ pF},$	f = 10 MHz	3.3 V	21.1	ηF
Opd	capacitance	Outputs enabled	CL = 50 pr,	I - IU MINZ	5 V	22.8	l bi i

6.12 Typical Characteristics

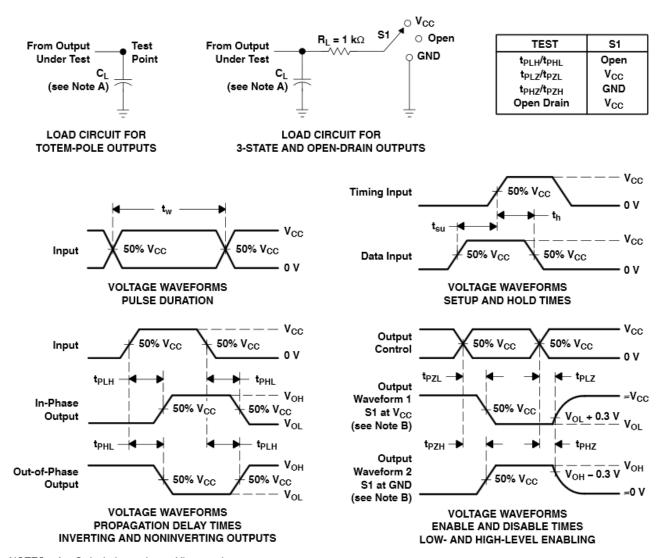




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7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_0 = 50 \Omega$, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. t_{PHL} and t_{PLH} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 7-1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LV374A devices are octal edge-triggered D-type flip-flops designed for 2 V to 5.5 V V_{CC} operation. These devices feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bi-directional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs. A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. \overline{OE} does not affect internal operations of the latch.

Old data can be retained or new data can be entered while the outputs are in the high-impedance state. To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for partial-power-down applications using loff. The loff circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The output of the device is unknown until the first valid rising clock edge occurs while V_{CC} is within the Section 6.3 range.

8.2 Functional Block Diagram

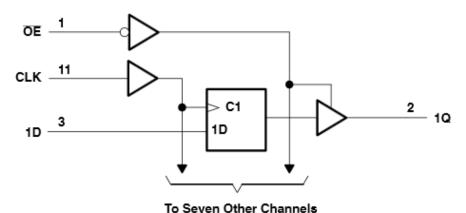


Figure 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

The device's wide operating range allows it to be used in a variety of systems that use different logic levels. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low ground bounce stabilizes the performance of non-switching outputs while another output is switching.

8.4 Device Functional Modes

Table 8-1 lists the functional modes of the SN74LV374A devices.

Table 8-1. Function Table (Each Flip-Flop)

	OUTPUT				
ŌĒ	CLK	D	Q		
L	↑	Н	Н		
L	↑	L	L		
L	L	Х	Q ₀		
Н	Х	Х	Z		

Submit Document Feedback



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LV374A is a low drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs accept voltages up to 5.5 V allowing down translation to the V_{CC} level.

9.2 Typical Application

Figure 9-1 shows how the slower edges can reduce ringing on the output compared to higher drive parts like AC.

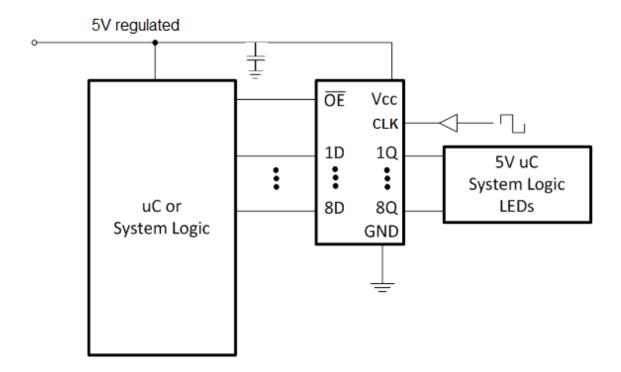


Figure 9-1. Typical Application Schematic

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so consider routing and load conditions to prevent ringing.

9.2.2 Detailed Design Procedure

- · Recommended Input conditions:
 - Rise time and fall time specs see ($\Delta t/\Delta V$) in Section 6.3.
 - Specified High and low levels. See (V_{IH} and V_{IL}) in Section 6.3.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid $V_{\rm CC}$.
- · Recommended output conditions:
 - Load currents should not exceed 35 mA per output and 70 mA total for the part.
 - Outputs should not be pulled above V_{CC}.

9.2.3 Application Curve

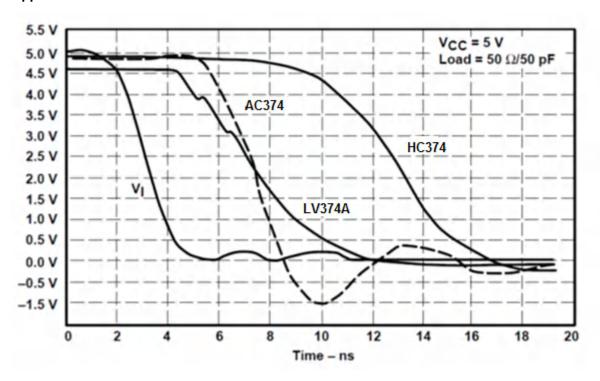


Figure 9-2. Switching Characteristics Comparison

9.3 Power Supply Recommendations

9.4 Layout

9.4.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only three of the four buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever make more sense or is more convenient. Floating outputs is generally acceptable, unless the part is a transceiver. If the transceiver has an output enable pin it will disable the outputs section of the part when asserted. This will not disable the input section of the I.O's so they also cannot float when disabled.



9.4.1.1 Layout Example



Figure 9-3. Layout Example

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

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10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV374ADBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples
SN74LV374ADW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples
SN74LV374ADWG4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples
SN74LV374ADWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples
SN74LV374ANSR	ACTIVE	SO	NS	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV374A	Samples
SN74LV374APW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples
SN74LV374APWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV374A	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LV374A:

Automotive: SN74LV374A-Q1

• Enhanced Product : SN74LV374A-EP

NOTE: Qualified Version Definitions:

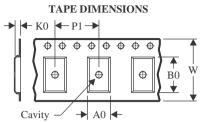
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV374ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LV374ADWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LV374ANSR	so	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LV374APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1



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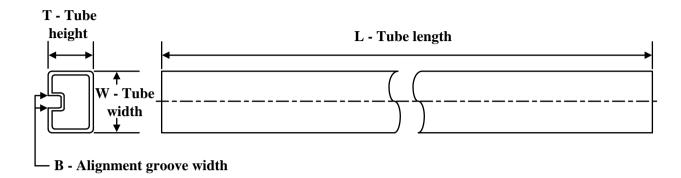
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV374ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LV374ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LV374ANSR	so	NS	20	2000	367.0	367.0	45.0
SN74LV374APWR	TSSOP	PW	20	2000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74LV374ADW	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LV374ADWG4	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LV374APW	PW	TSSOP	20	70	530	10.2	3600	3.5



SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
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NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



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